- Wide Supply Voltage Range: 4.5V - 24V
- 4A Peak Source Current and 4A Peak Sink Current
- Negative Input Voltage Capability: Down to -5V
- TTL Compatible Input Logic Threshold
- Propagation Delay: 13ns
- Typical Rising and Falling Times: 8ns
- Thermal Shutdown Protection: 170℃
- Available in SOP-8 Package

- IGBT/MOSFET Gate Driver
- Variable Frequency-Drive (VFD)
- Switching Power Supply
- Motor Control
- Solar Power Inverter

The SCT52245 is a wide supply, dual channel, high speed, low side gate drivers for both power MOSFET and IGBT. Each channel can source and sink 4A peak current along with rail-to-rail output capability. The 24V power supply rail enhances the driver output ringing endurance during the power device transition.

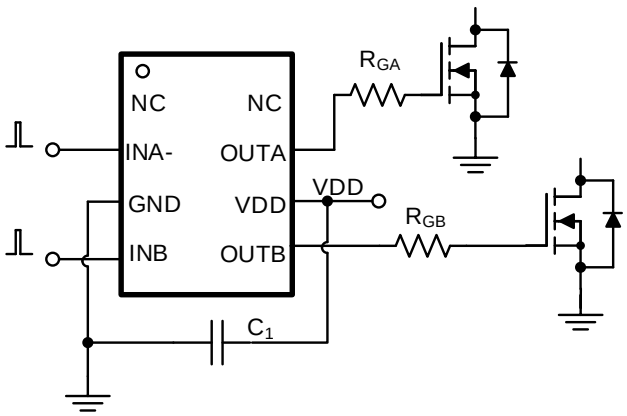
The minimum 13ns input to output propagation delay enables the SCT52245 suitable for high frequency power converter application.

The SCT52245 features wide input hysteresis that is compatible for TTL low voltage logic. The SCT52245 has the capability to handle negative input down to -5V, which increases the input noise immunity.

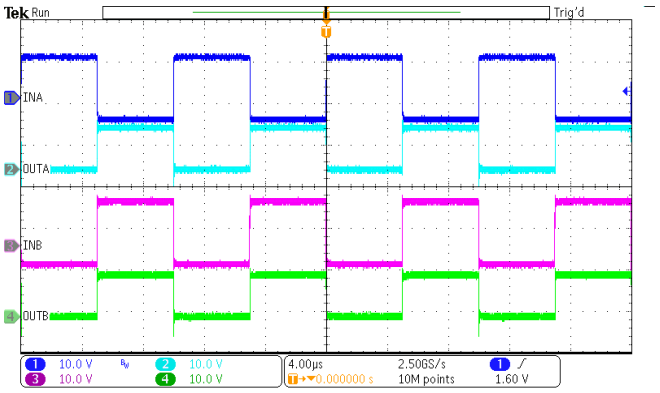
The SCT52245 has very low quiescent current that reduces the stand-by loss in the power converter. The SCT52245 each channel driver adopts non-overlap driver design to avoid the shoot-through of output stage.

The SCT52245 features 170℃ thermal shut down. The SCT52245 is available in SOP-8 package

SCT52245 Typical Application



Application Waveform



NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Revision 1.0: Production

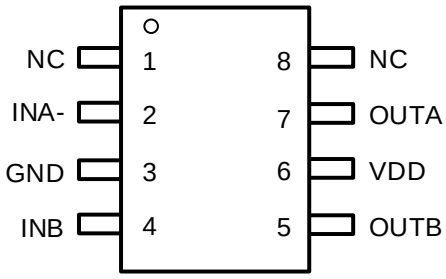
Revision 1.1: Update DEVICE ORDER INFORMATION

ORDERABLE DEVICE	PACKAGING TYPE	STANDARD PACK QTY	PACKAGE MARKING	PINS	PACKAGE DESCRIPTION
SCT52245STDR	Tape & Reel	4000	2245	8	SOP-8L

Over operating free-air temperature unless otherwise noted(1)

DESCRIPTION	MIN	MAX	UNIT
INA-, INB	-5	26	V
OUTA, OUTB	-0.3	VDD+0.3	V
VDD	-0.3	26	V
Operating junction temperature TJ (2)	-40	150	℃
Storage temperature T_{STG}	-65	150	℃

Top View: SOP-8pin Plastic



(1) Stresses beyond those listed under Absolut Maximum Rating may cause device permanent damage. The device is not guaranteed to function outside of its Recommended Operation Conditions.

(2) The IC includes over temperature protection to protect the device during overload conditions. Junction temperature will exceed 150℃ when over temperature protection is active. Continuous operation above the specified maximum operating junction temperature will reduce lifetime.

NAME	NO.	PIN FUNCTION
NC	1	No Connection.
INA-	2	Channel A logic input, TTL compatible. Floating logic low.
GND	3	Power ground. Must be soldered directly to ground plane for thermal performance improvement and electrical contact.
INB	4	Channel B logic input, TTL compatible. Floating logic low.
OUTB	5	Channel B gate driver output
VDD	6	Power Supply, must be locally bypassed by the ceramic cap.
OUTA	7	Channel A gate driver output
NC	8	No Connection.

Over operating free-air temperature range unless otherwise noted

PARAMETER	DEFINITION	MIN	MAX	UNIT
V_{DD}	Supply voltage range	4.5	24	V
$V_{INA-,INB}$	Input voltage range	-5	24	
T_J	Operating junction temperature	-40	150	℃

PARAMETER	DEFINITION	MIN	MAX	UNIT
V_{ESD}	Human Body Model (HBM), per ANSI-JEDEC-JS-001-2014 specification, all pins (1)	-2	+2	kV

V_{DD}=12V, T_J=-40℃ ~150℃, typical value s are tested under 25℃.

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
Power Supply and Output						
V_{DD}	Operating supply voltage		4.5		24	V
V_{DD_UVLO}	Input UVLO Hysteresis	V_{DD} rising		4.2 300	4.5	V mV
I_Q	Supply current	V_{DD}=12V, INA- =INB =GND		130		uA
		V_{DD}=12V, INA- =INB =12V		190		uA
INPUTS						
V_{INA-,INB_H}	Input logic high threshold Output low for inverting input Output high for non-inverting input			2.1	2.4	V
V_{INA-,INB_L}	Input logic low threshold Output high for inverting input Output low for non-inverting input		0.8	1		V
V_{IN_Hys}	Hysteresis			1.1		V
OUTPUTS						
$V_{DD}\_V_{OH}$	Output output high voltage	I_{OUT}= - 10mA			150	mV
V_{OL}	Output low voltage	I_{OUT}= 10mA			10	mV
$I_{SINK/SRC}$	Output sink/source peak current	C_{Load}=10nF, F_{SW}=1kHz		4		A
R_{OH}	Output pull high resistance (only PMOS ON)	I_{OUT}= - 10mA	5	9	18	
R_{OL}	Output pull low resistance	I_{OUT}= 10mA	0.3	0.6	1.2	
Timing						
T_R	Output rising time	C_{Load}=1nF		8	20	ns
T_F	Output falling time	C_{Load}=1nF		8	20	ns
T_{D_IN}	Input to output propagation delay, Rising edge			13	25	ns
	Input to output propagation delay, Falling edge			13	25	ns
T_{MIN_ON}	Minimum input pulse width	C_{Load}=1nF		20	30	ns
Protection						
T_{SD}	Thermal shutdown threshold*	T_J rising		170		℃
	Hysteresis			25		℃

*Derived from bench characterization

V_{IN}=12V, T_A= 25℃.

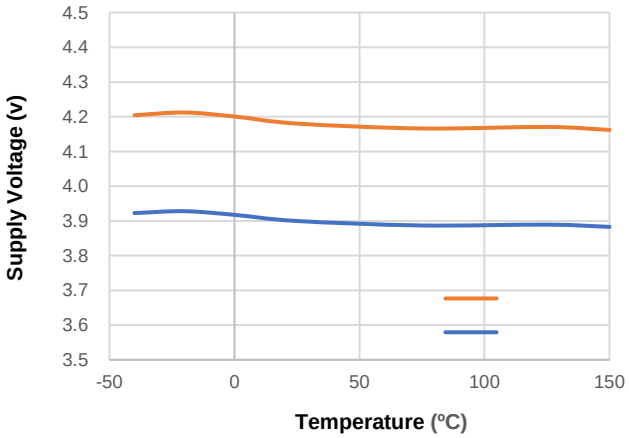


Figure 1. UVLO vs Temperature

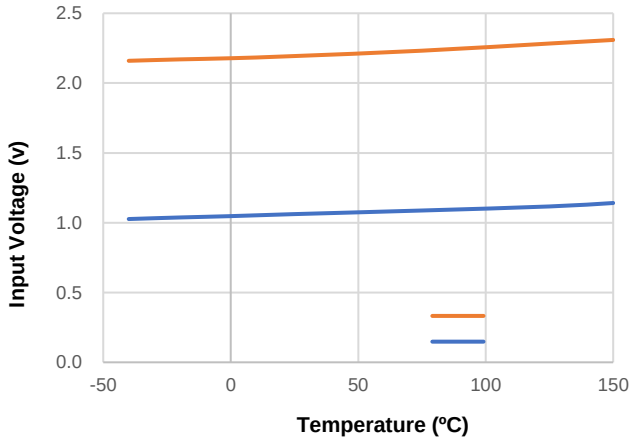


Figure 2. Input Threshold vs Temperature

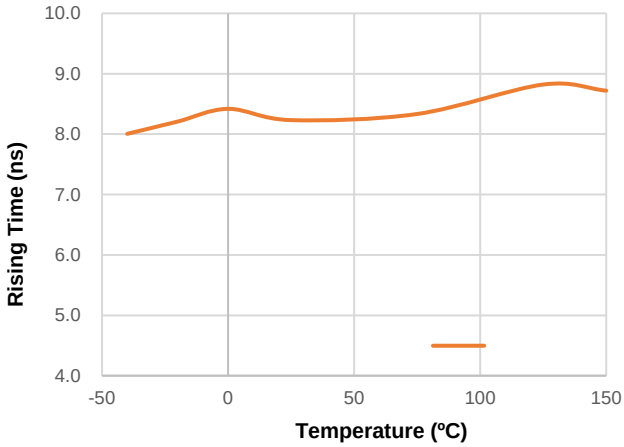


Figure 3 Output Rising Time vs Temperature

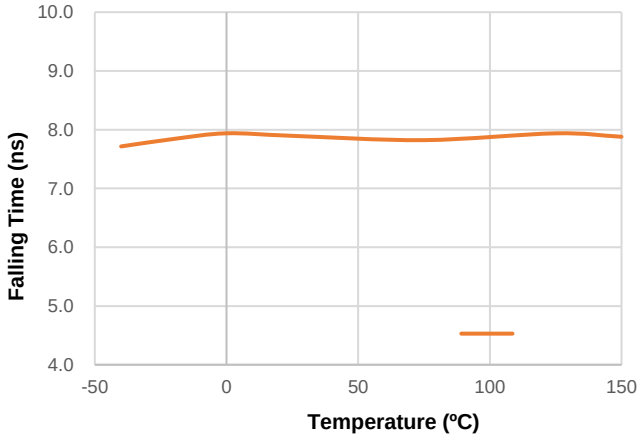


Figure 4. Output Falling Time vs Temperature

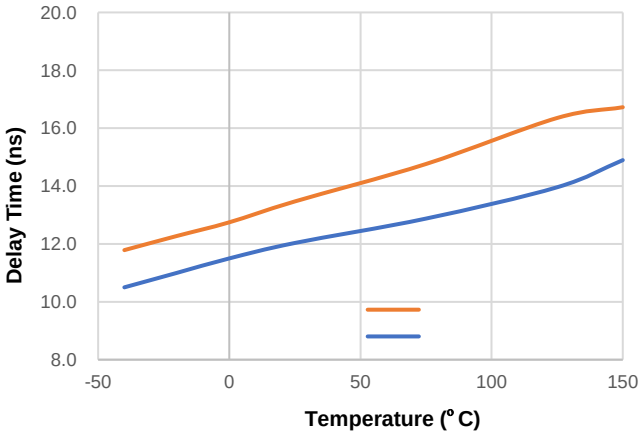


Figure 5. Input to Output Propagation Delay vs Temperature

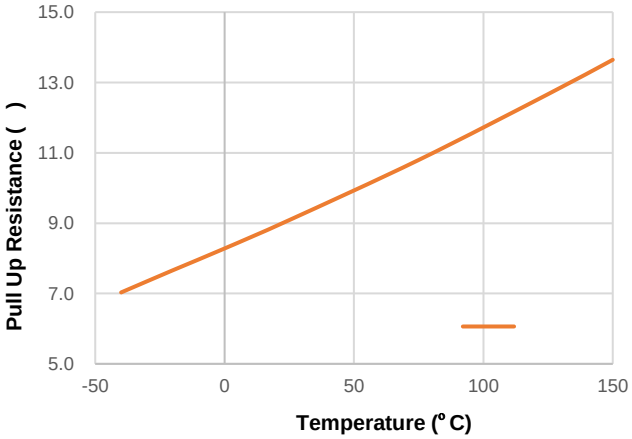


Figure 6. ROH vs Temperature

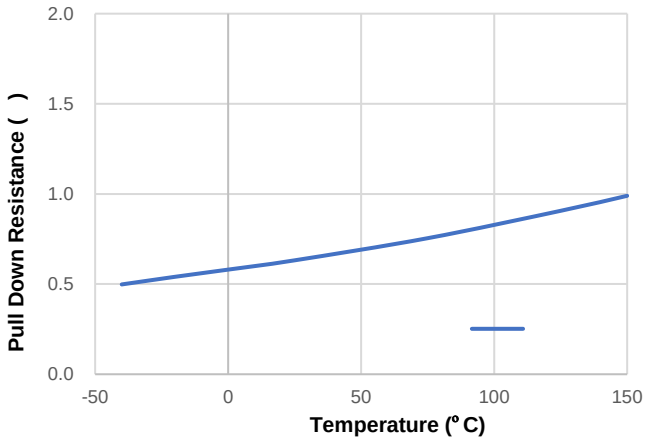


Figure 7. ROL vs Temperature

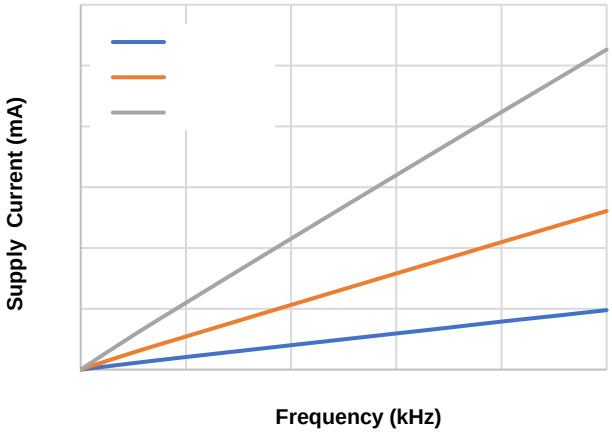


Figure 8. Operation Supply Current vs Frequency, C_{OUT}=1nF

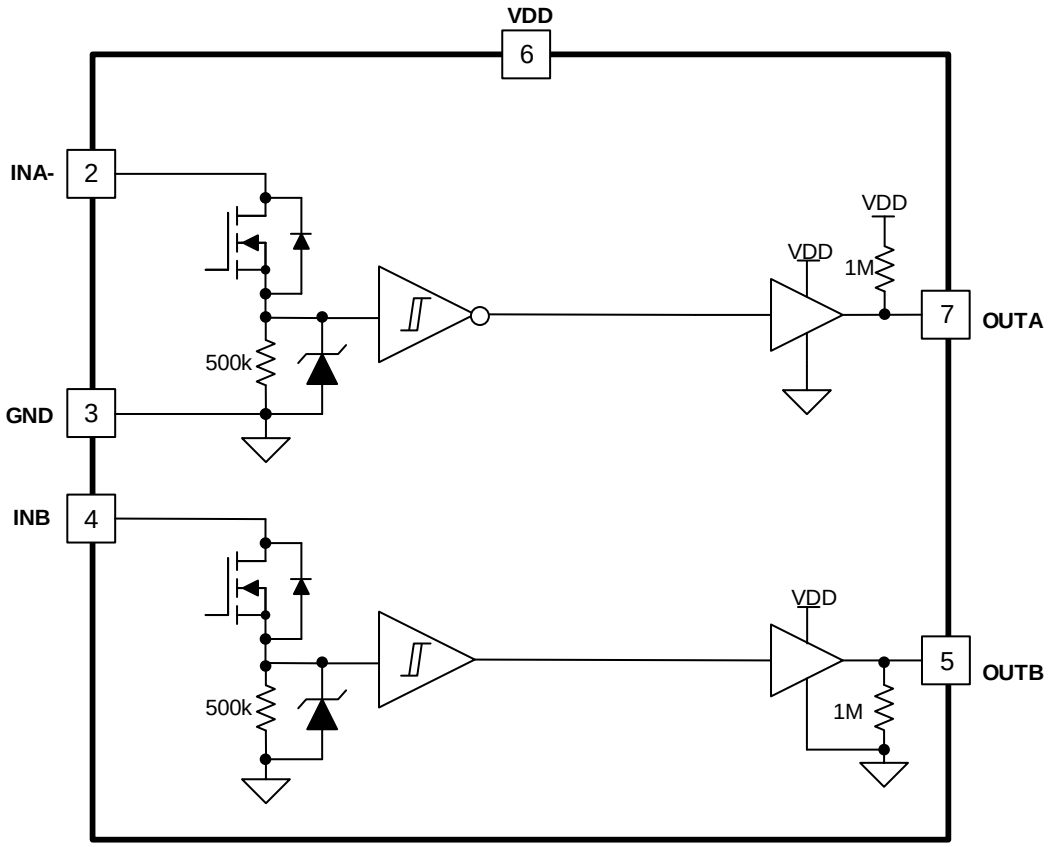


Figure 9. Functional Block Diagram

across temperature. The very low input parasitic capacitance on the input pins increases switching speed and reduces the propagation delay.

Output Stage

The SCT52245 output stage features the pull up structure with P-type MOSFET PM1 and N-type MOSFET NM1 in parallel, as shown in Figure 12. PM1 provides the pull up capability when OUT approaches VDD and the NM1 holds off state, which guarantees the driver output is up to VDD rail. The measurable on-resistance R_{OH} in steady state is the conduction resistance of PM1. NM1 provides a narrow instant peak sourcing current up to 4A to eliminate the turn on time and delay. During the output turn on transition, the equivalent hybrid pull on transient resistance is $1.5R_{OL}$, which is much lower than the DC measured R_{OH}.

The N-type MOSFET NM2 composes the output stage pull down structure; the R_{OL} is the DC measurement and represents the pull down impedance. The output stage of SCT52245 provides rail-to-rail operation, and is able to supply 4A sourcing and 4A sinking peak current. The presence of the MOSFET-body diodes also offers low impedance to switching overshoots and undershoots. The outputs of the dual channel drivers are designed to withstand 500-mA reverse current without either damaging the device or logic malfunction.

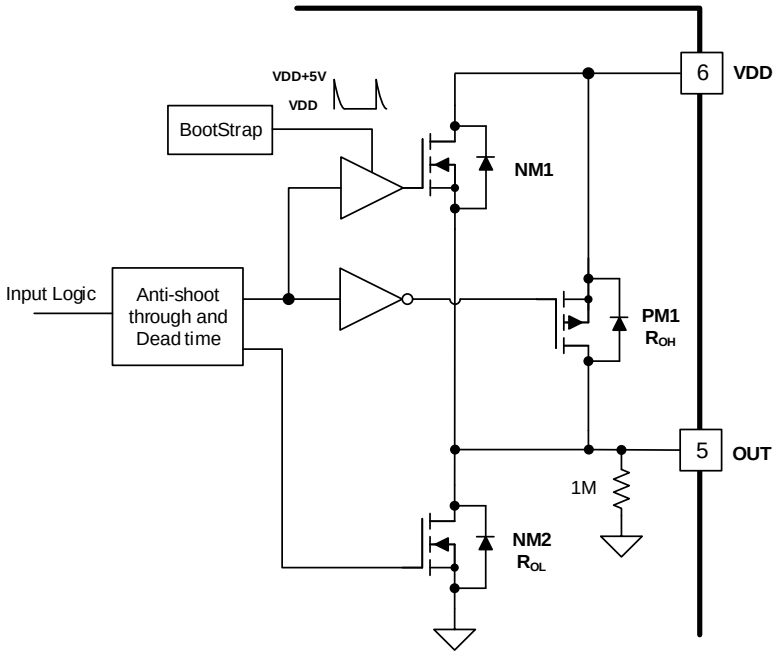


Figure 10. SCT52245 Channel-B Output Stage

Thermal Shutdown

Once the junction temperature in the SCT52245 exceeds 170° C, the thermal sensing circuit stops switching until the junction temperature falling below 145° C, and the device restarts. Thermal shutdown prevents the damage on device during excessive heat and power dissipation condition.

Typical Application

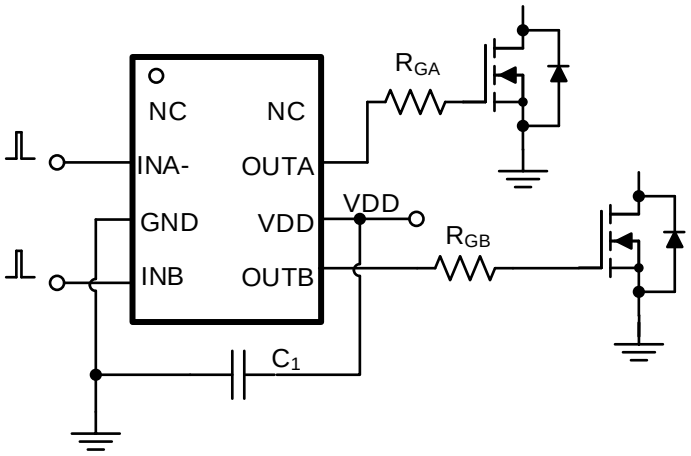


Figure 11. Dual Channel Driver Typical Application

Driver Power Dissipation

Generally, the power dissipated in the SCT52245 depends on the gate charge required of the power device (Qg), switching frequency, and use of external gate resistors. The SCT52245 features very low quiescent currents and internal logic to eliminate any shoot-through in the output driver stage, their effect on the power dissipation within the gate driver is negligible.

For the pure capacitive load, the power loss of each channel in SCT52245 is:

(1)

Where

- V_{DD} is supply voltage
- C_{Load} is the output capacitance
- F_{SW} is the switching frequency

For the the switching load of power MOSFET, the power loss of each channel in the SCT52245 is shown in equation (2), where charging a capacitor is determined by using the equivalence $Q_g = C_{LOAD}V_{DD}$. The gate charge includes the effects of the input capacitance plus the added charge needed to swing the drain voltage of the power device as it switches between the ON and OFF states. Manufacturers provide specifications that provide the typical and maximum gate charge, in nC, to switch the device under specified conditions.

(2)

Where

- Q_g is the gate charge of the power device
- f_{SW} is the switching frequency
- V_{DD} is the supply voltage

If R_G applied between driver and gate of power device to slow down the power device transition, the power dissipation of the driver shows as below:

(3)

Application Waveforms

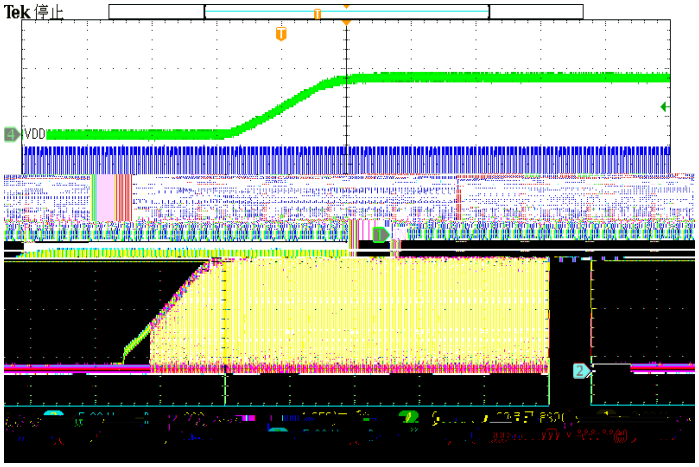


Figure 12. VDD Power ON

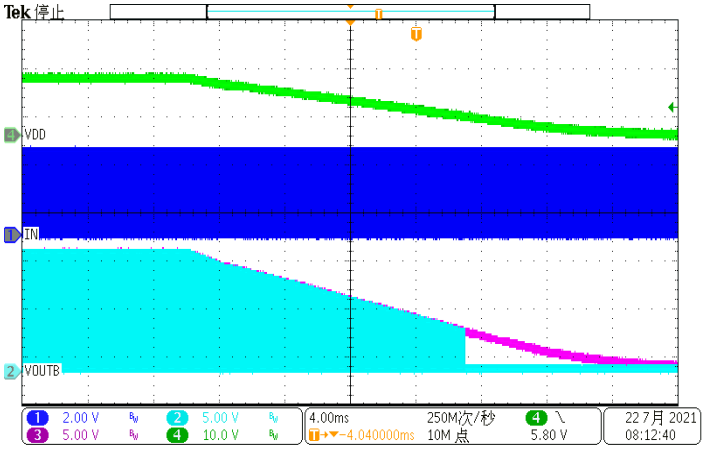


Figure 13. VDD Power OFF

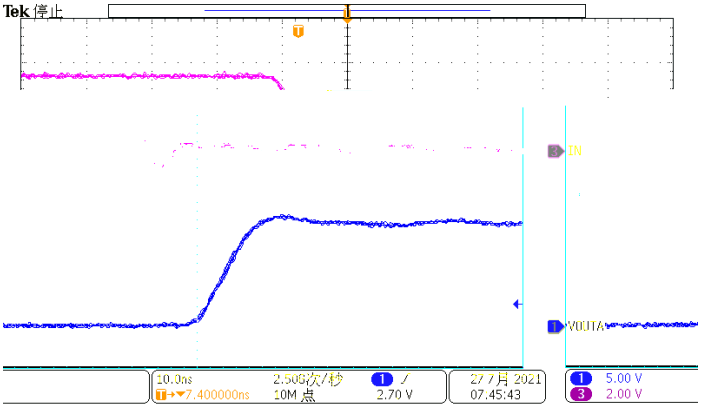


Figure 14. OUTA Switching Rise (C = 1)

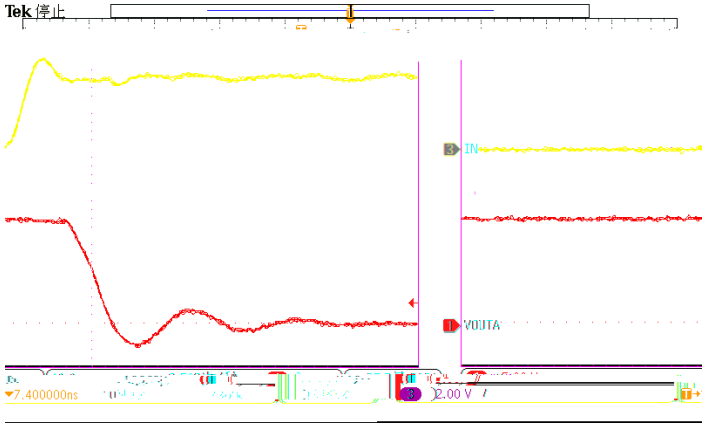


Figure 15. OUTA Switching Fall (C = 1)

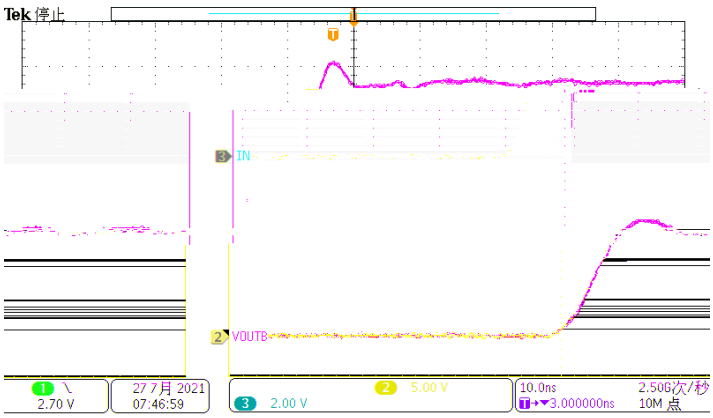


Figure 16. OUTB Switching Rise (C = 1)

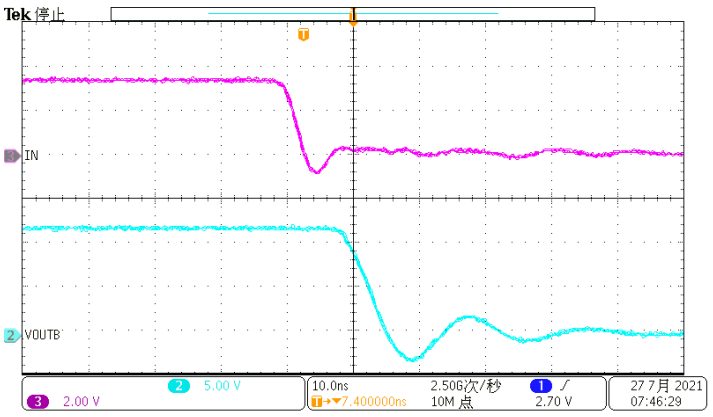


Figure 17. OUTB Switching Fall (C = 1)

Layout Guideline

The SCT52245 provides the 4A output driving current and features very short rising and falling time at the power devices gate. The high di/dt causes driver output unexpected ringing when the driver output loop is not designed well. The regulator could suffer from malfunction and EMI noise problems if the power device gate has serious ringing. Below are the layout recommendations with using SCT52245 and Figure 1

The real junction-to-ambient thermal resistance R of the package greatly depends on the PCB type, layout, and environmental factor. Soldering the ground pin to a large ground plate enhance the thermal performance. Using more vias connects the ground plate on the top layer and bottom layer around the IC without solder mask also improves the thermal capability.

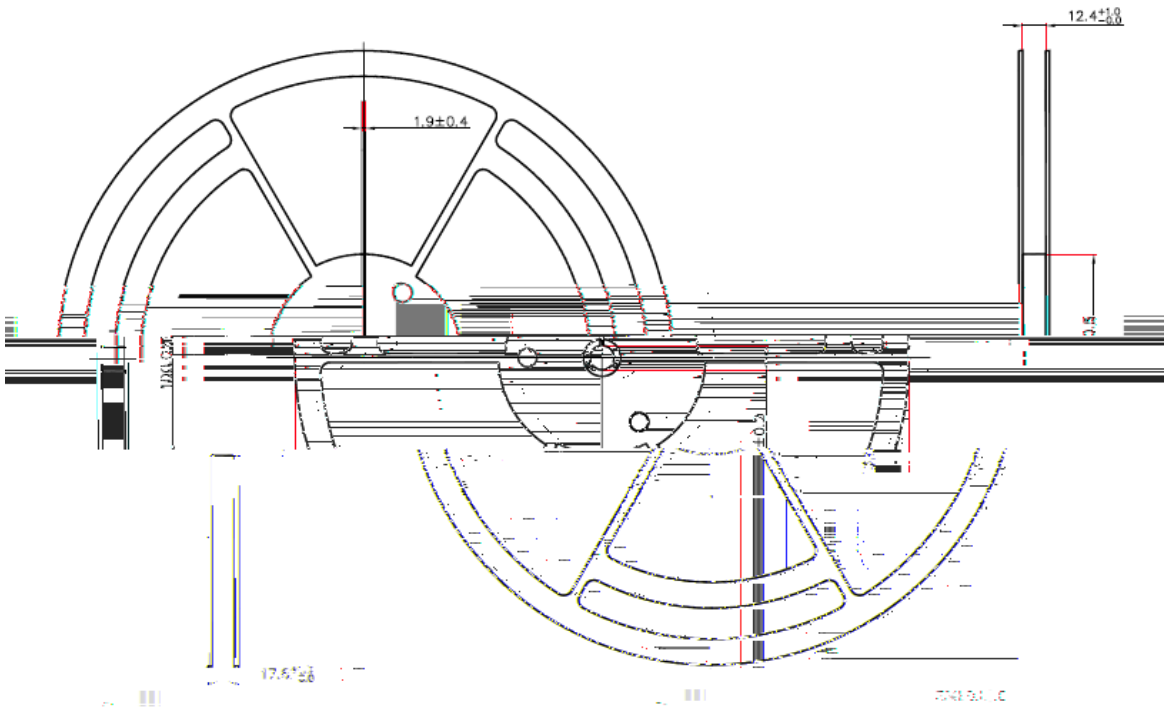
TOP VIEW

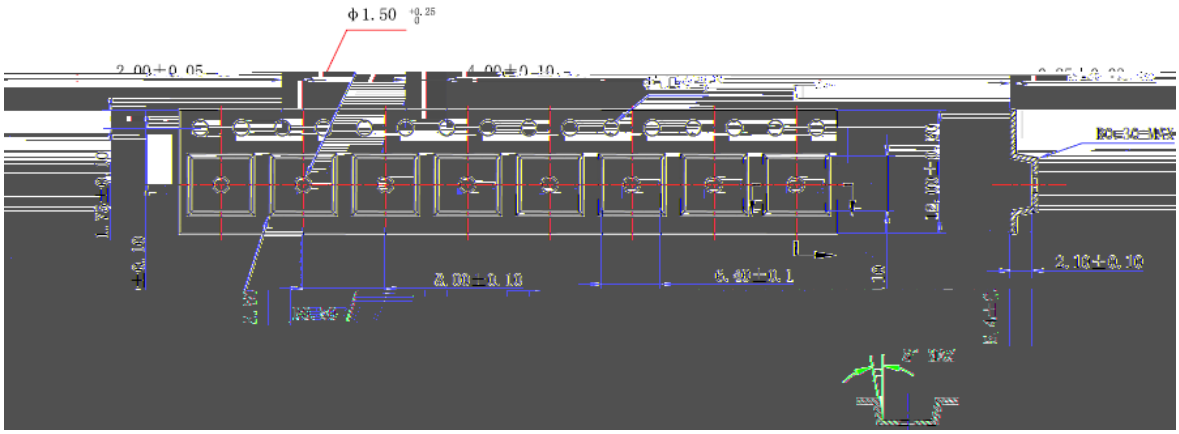
BOTTOM VIEW

SIDE VIEW

NOTE:

1. Drawing proposed to be made a JEDEC package outline MO-220 variation.
2. Drawing not to scale.
3.





Feeding Direction

